



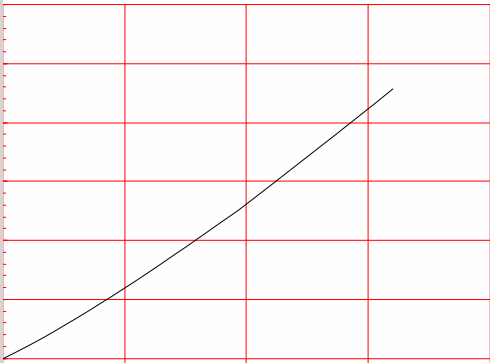
|                                                                      |          |     |    |
|----------------------------------------------------------------------|----------|-----|----|
| Peak pulse voltage<br>( $T_j=25$ ; non-repetitive, off-state; FIG.7) | $V_{pp}$ | 4.5 | kV |
|----------------------------------------------------------------------|----------|-----|----|

**ELECTRICAL CHARACTERISTICS** ( $T_j=25$  unless otherwise specified)

| Symbol      | Test Condition                              | Quadrant | Value |     | Unit       |
|-------------|---------------------------------------------|----------|-------|-----|------------|
| $I_{GT}$    | $V_D=12V$ $R_L=33\Omega$                    | - -      | MAX.  | 5   | mA         |
|             |                                             |          |       | 10  |            |
| $V_{GT}$    |                                             | ALL      | MAX.  | 1   | V          |
| $V_{GD}$    | $V_D=V_{DRM}$ $T_j=125$<br>$R_L=3.3k\Omega$ | ALL      | MIN.  | 0.2 | V          |
| $I_L$       | $I_G=1.2I_{GT}$                             | - -      | MAX.  | 15  | mA         |
|             |                                             |          |       | 20  |            |
| $I_H$       | $I_T=500mA$                                 |          | MAX.  | 10  | mA         |
| $dV/dt$     | $V_D=540V$ Gate Open $T_j=125$              |          | MIN.  | 40  | V/ $\mu s$ |
| $(dV/dt)_c$ | $(dI/dt)_c=7.2A/ms$ , $T_j=10$              |          | MIN.  | 2   | V/ $\mu s$ |



**FIG.1:** Maximum power dissipation versus RMS on-state current



**FIG.2:** RMS on-state current versus case temperature







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